

**33 EDS Members Elected to the IEEE Grade of Fellow
Effective 1 January 2001**

Peter M. Asbeck

University of California, San Diego, La Jolla, CA, USA

For development of heterostructure bipolar transistors and applications

Werner Bachtold

Swiss Federal Institute of Technology, Zurich, Switzerland

For contributions to the development of microwave semiconductor devices and circuits

Jeffrey Bokor

University of California, Berkeley, Berkeley, CA, USA

For contributions to EUV optical lithography and deep-submicron MOSFETs

Elliott Rave Brown

University of California, Los Angeles, Los Angeles, USA

For contributions to microwave and millimeter-wave solid-state antennas and sources

Stephen Y. Chou

Princeton University, Princeton, NJ, USA

For contributions to the development of nanoscale electronic devices and nanotechnology

Michael J. Declercq

Swiss Federal Institute of Technology, Lausanne, Switzerland

For contributions to innovate design of mixed signal integrated circuits

Steven W. Depp

IBM T.J. Watson Research Center, Yorktown Heights, NY, USA

For contributions to thin film transistor/liquid crystal display technology

Sverre T. Eng

Jet Propulsion Laboratory, Pasadena, CA, USA

For contributions to optical communications, applied laser spectroscopy, and low-noise mixer diode technology

Tor Arne Fjeldly

Norwegian University of Science & Technology, Kjeller, Norway

For contributions to semiconductor device modeling and the development of AIM spice

Eby Gershon Friedman

University of Rochester, Rochester, NY, USA

For contributions to high performance circuit design and VLSI-based synchronous systems

Daniel Charles Guterman

SanDisk Corporation, Sunnyvale, CA, USA

For leadership in the development of non-volatile, solid-state memory technologies

Ronald W. Knepper

IBM Microelectronics, SRDC, Hopewell Junction, NY, USA

For contributions to semiconductor device design, modeling, and circuits

Robert Michael Kolbas

North Carolina State University, Raleigh, NC, USA

For contributions to understanding and development of quantum well heterostructure laser and light emitters

James B. Kuo

National Taiwan University, Taipei, Taiwan

For contributions to modeling CMOS VLSI devices

Lawrence Ernest Larson

For contributions to development and applications of high-speed integrated circuits and devices

Chien-Ping Lee

National Chiao Tung University, Hsin Chu, Taiwan

For contributions to optoelectronic integrated circuits and compound semiconductor devices and technology

John Haig Marsh

University of Glasgow, Glasgow, Scotland

For contributions to development of integrated optics based on semiconductor quantum well devices

Masatoshi Migitaka

Toyota Technological Institute, Nagoya, Japan

For contributions to research and development of silicon high temperature integrated circuits

Vijay K. Nair

Motorola Research Labs, Tempe, AZ, USA

For contributions to development of low-power device and integrated circuits

Khalil Najafi

University of Michigan, Ann Arbor, MI, USA

For contributions to biomedical microelectromechanical systems technology

Yi-Ching Pao

Filtronic Solid State, Inc., Santa Clara, CA, USA

For contributions to the development and manufacturing of molecular beam epitaxial based microwave and millimeter-wave devices and integrated circuits

David L. Pulfrey

University of British Columbia, Vancouver, Canada

For contributions to the modeling of heterojunction bipolar semiconductor devices

Conor S. Rafferty

Lucent Technologies, Murray Hill, NJ, USA

For the development of pioneering simulation tools and models for technology computer aided design

Ronald D. Schrimpf

Vanderbilt University, Nashville, TN, USA

For contributions to the understanding and the modeling of physical mechanisms governing the response of semiconductor devices to radiation exposure

Eric Fred Schubert

Boston University, Boston, MA, USA

For contributions to semiconductor doping and resonant-cavity devices

Joannes M.J. Sevenhans

Alcatel, Antwerpen, Belgium

For contributions to the design of solid-state telecommunications transceivers

Rainee Navin Simons

For contributions to development of microwave coplanar transmission lines and circuits

Costas John Spanos

University of California, Berkeley, Berkeley, CA, USA

For contributions and leadership in semiconductor manufacturing

Yuan-Chen Sun

Taiwan Semiconductor Manufacturing Company, Hsin-Chu, Taiwan

For contributions to advanced CMOS technology

Federico Tosco

CSELT, Torino, Italy

For contributions and leadership in technologies and international standards for optical and wireless communications

Sigurd Wagner

Princeton University, Princeton, NJ, USA

For contributions to copper indium selenide and amorphous silicon thin-film solar cells and contributions to engineering education

Bogdan Maciej Wilamowski

University of Wyoming, Laramie, WY, USA

For contributions to industrial electronics and static induction devices

Naoki Yokoyama

Fujitsu Laboratories, Ltd., Atsugi, Japan

For contributions to the development of self-aligned gallium arsenide MESFET integrated circuits